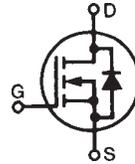


High Voltage MOSFET IXTP05N100M

(Electrically Isolated Tab)

N-Channel Enhancement Mode
Avalanche Rated

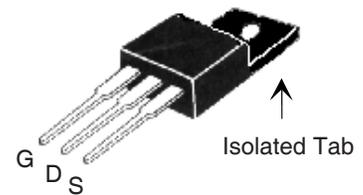


$$V_{DSS} = 1000V$$

$$I_{D25} = 700mA$$

$$R_{DS(on)} \leq 17\Omega$$

OVERMOLDED TO-220
(IXTP...M) OUTLINE



G = Gate D = Drain
S = Source

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	1000	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1 M\Omega$	1000	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ C$	700	mA
I_{DM}	$T_C = 25^\circ C$, pulse width limited by T_{JM}	3	A
I_A	$T_C = 25^\circ C$	1	A
E_{AS}	$T_C = 25^\circ C$	100	mJ
dv/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J = 150^\circ C$	3	V/ns
P_D	$T_C = 25^\circ C$	25	W
T_J		- 55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		- 55 ... +150	$^\circ C$
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ C$
T_{SOLD}	Plastic body for 10 s	260	$^\circ C$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight		2.5	g

Features

- Plastic overmolded tab for electrical isolation
- International standard package
- Avalanche rated
- Low package inductance
 - easy to drive and to protect

Advantages

- Easy to mount
- Space savings
- High power density

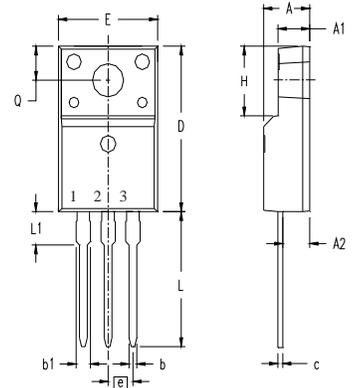
Symbol	Test Conditions ($T_J = 25^\circ C$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 25\mu A$	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 30V$, $V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0V$ $T_J = 125^\circ C$			25 μA 500 μA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 375mA$, Note 1		15	17 Ω

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{V}$, $I_D = 500\text{mA}$, Note 1	0.55	0.93	S
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		260	pF
C_{oss}			22	pF
C_{rss}			8	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 1\text{A}$ $R_G = 47\Omega$ (External)		11	ns
t_r			19	ns
$t_{d(off)}$			40	ns
t_f			28	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 1\text{A}$		7.8	nC
Q_{gs}			1.4	nC
Q_{gd}			4.1	nC
R_{thJC}				5.0 $^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$ unless otherwise specified)		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			750 mA
I_{SM}	Repetitive, pulse width limited by T_{JM}			3 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1			1.5 V
t_{rr}	$I_F = 750\text{mA}$, $-di/dt = 100\text{A}/\mu\text{s}$, $V_R = 100\text{V}$, $V_{GS} = 0\text{V}$		710	ns

ISOLATED TO-220 (IXTP...M)



Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.177	.193	4.50	4.90
A1	.092	.108	2.34	2.74
A2	.101	.117	2.56	2.96
b	.028	.035	0.70	0.90
b1	.050	.058	1.27	1.47
c	.018	.024	0.45	0.60
D	.617	.633	15.67	16.07
E	.392	.408	9.96	10.36
e	.100 BSC		2.54 BSC	
H	.255	.271	6.48	6.88
L	.499	.523	12.68	13.28
L1	.119	.135	3.03	3.43
$\varnothing P$.121	.129	3.08	3.28
Q	.126	.134	3.20	3.40

Notes: 1. Pulse test, $t \leq 300 \mu\text{s}$; duty cycle, $d \leq 2\%$.

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ 25°C

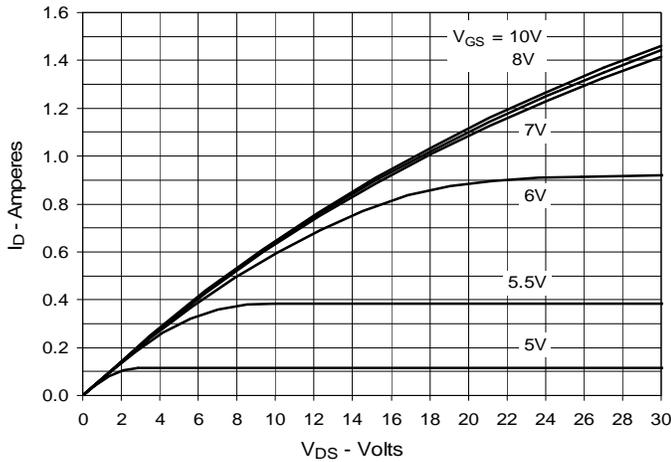


Fig. 2. Output Characteristics @ 125°C

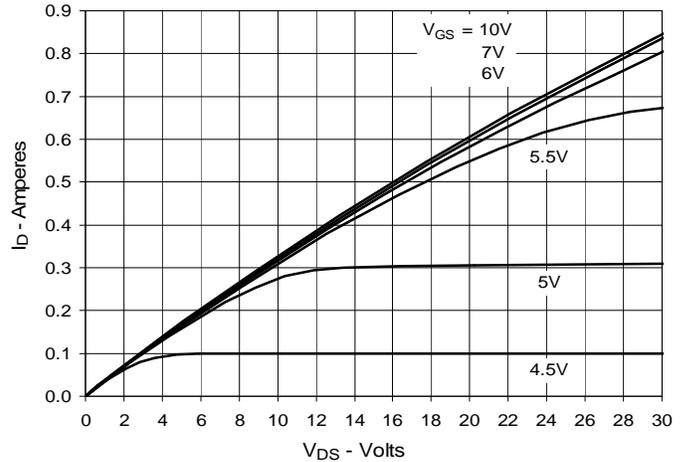


Fig. 3. $R_{DS(on)}$ Normalized to $I_D = 375mA$ Value vs. Junction Temperature

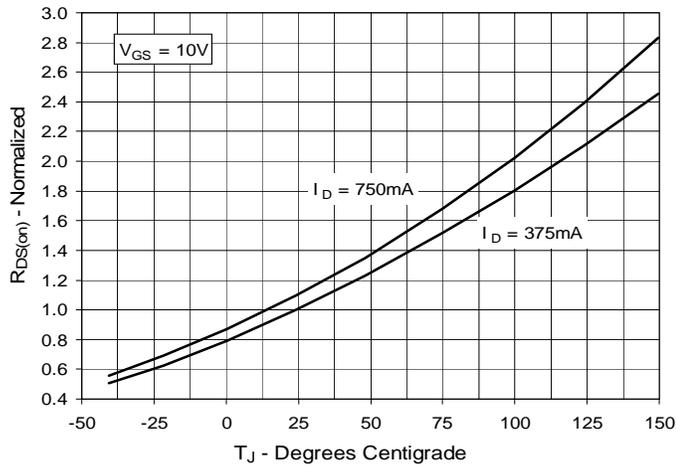


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 375mA$ Value vs. Drain Current

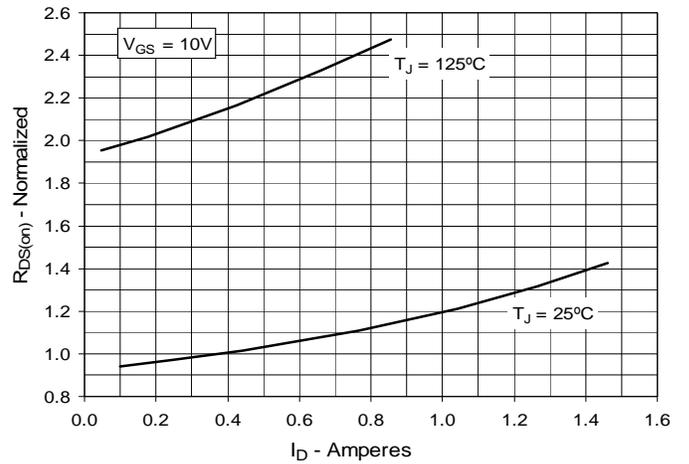


Fig. 5. Maximum Drain Current vs. Case Temperature

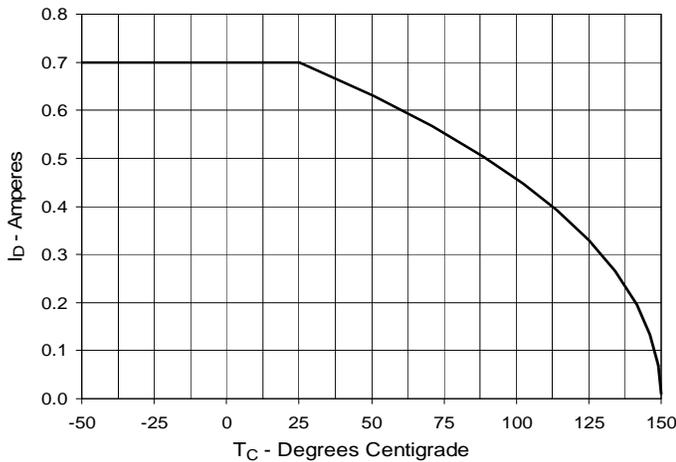


Fig. 6. Input Admittance

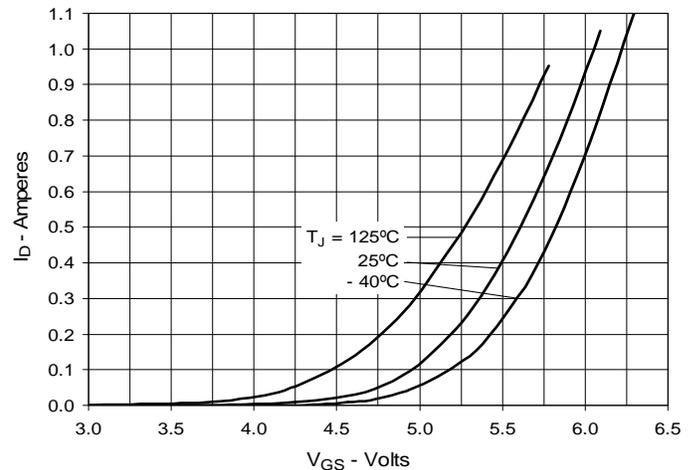


Fig. 7. Transconductance

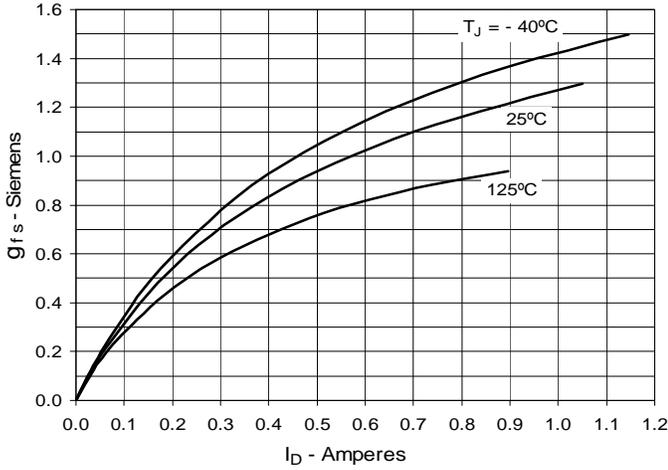


Fig. 8. Forward Voltage Drop of Intrinsic Diode

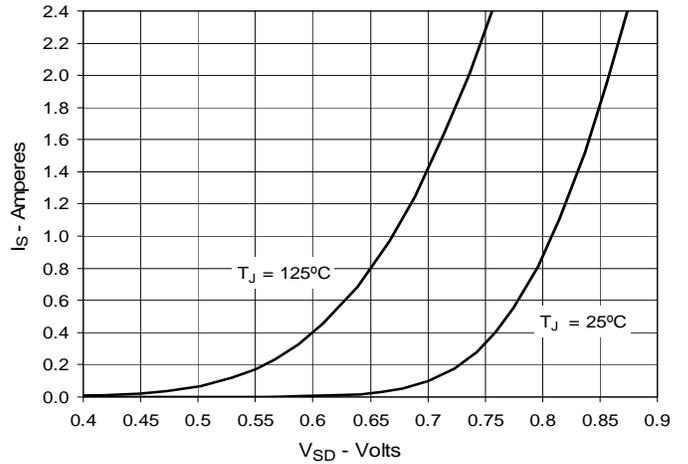


Fig. 9. Gate Charge

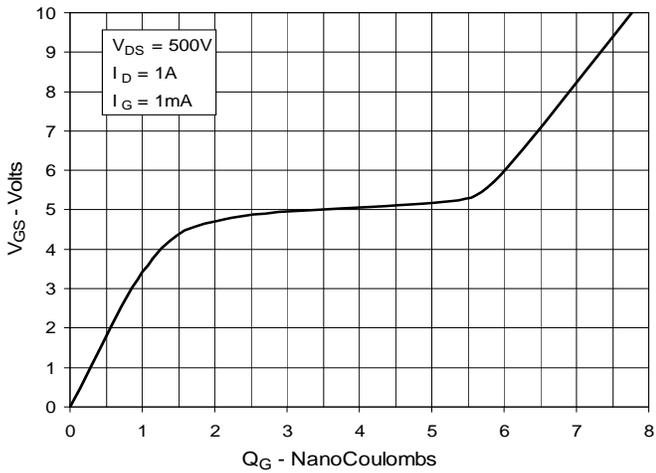


Fig. 10. Capacitance

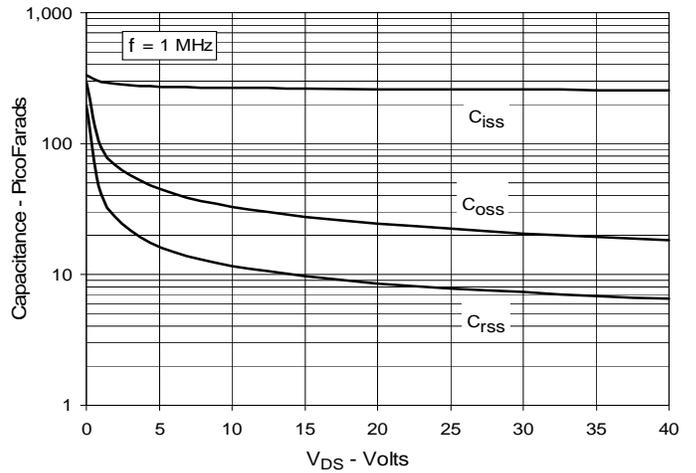
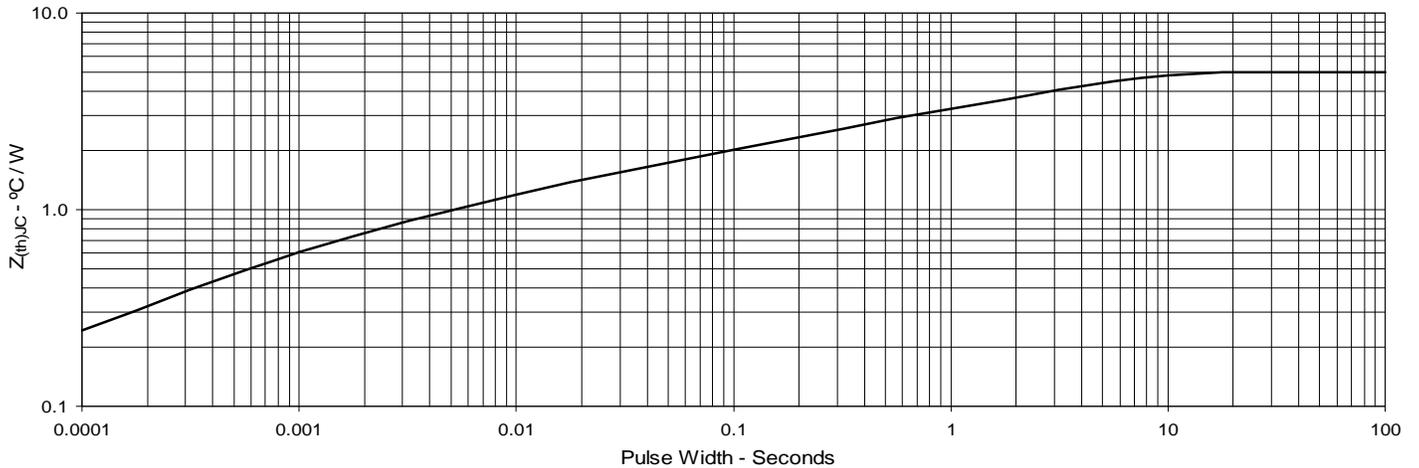


Fig. 11. Maximum Transient Thermal Impedance



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